

2SD1730

Silicon PNP Triple-Diffused Planar Type

Horizontal Deflection Output

Features

- Damper diode built-in
- Minimizes external component counts and simplifies circuitry
- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)

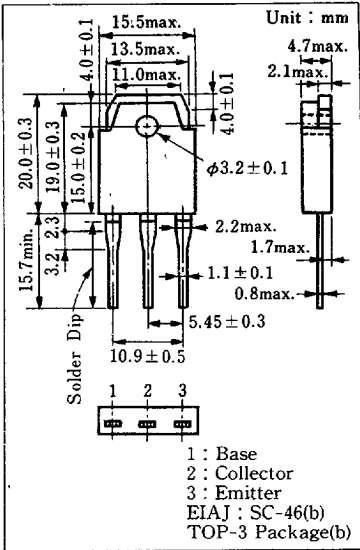
Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V _{CB0}	1500	V
Collector-emitter voltage	V _{CE5}	1500	V
	V _{CE0}	700	V
Emitter-base voltage	V _{EB0}	7	V
Peak collector current	I _{CP}	15	A
Collector current	I _C	5	A
Base current	I _B	2	A
Collector power dissipation	P _C	100	W
		2.5	
Junction temperature	T _J	150	°C
Storage temperature	T _{str}	-55 ~ +150	°C

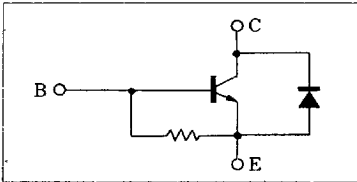
Electrical Characteristics (Tc=25°C)

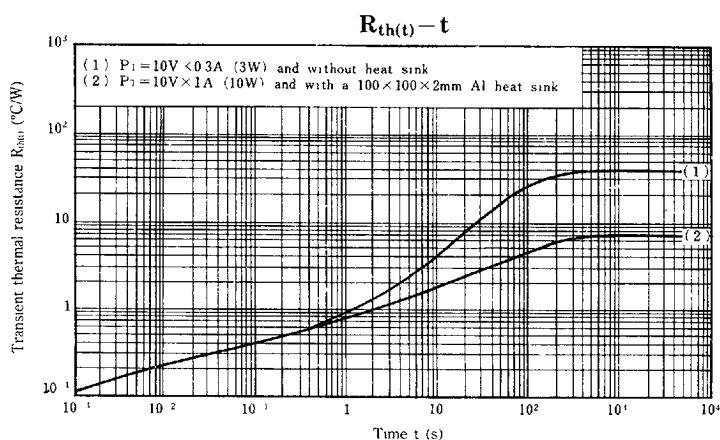
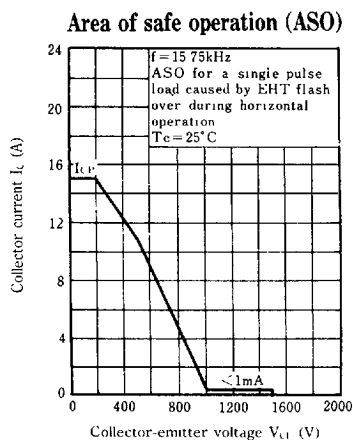
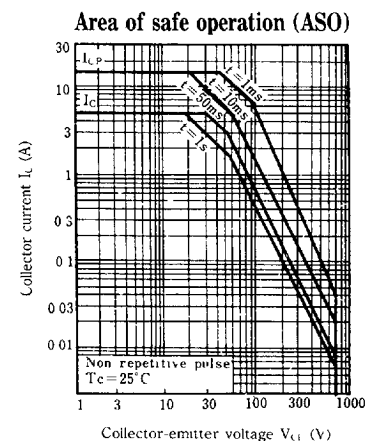
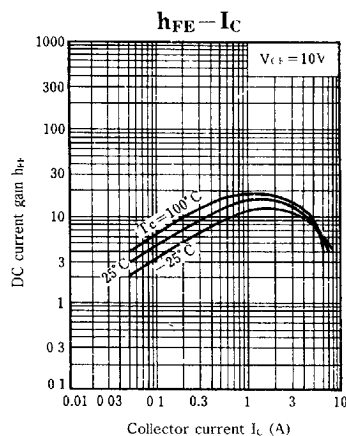
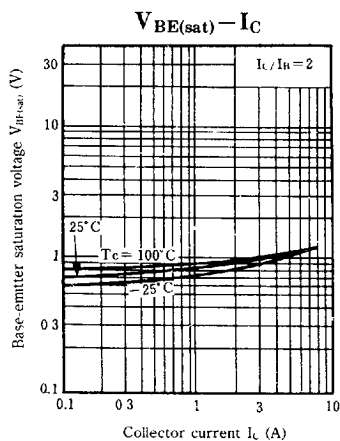
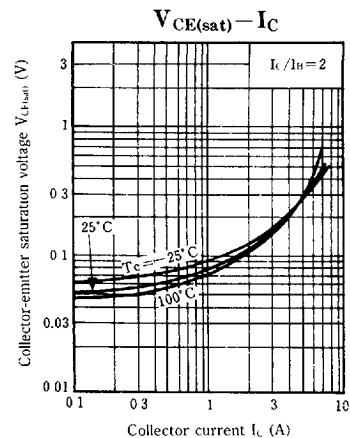
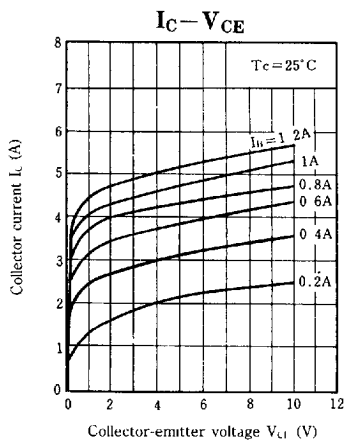
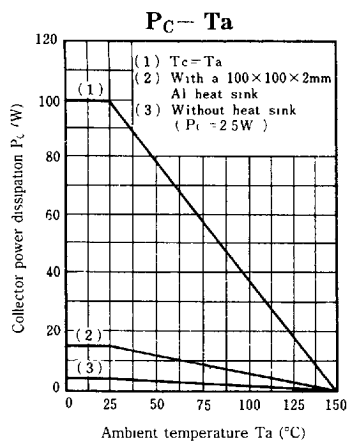
Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 750 V, I _E = 0			10	μA
		V _{CB} = 1500 V, I _B = 0			1	mA
Emitter-base voltage	V _{EB0}	I _E = 500 mA, I _C = 0	7			V
DC current gain	h _{FE}	V _{CE} = 5 V, I _C = 1 A	5		25	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 4 A, I _B = 1 A			8	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 4 A, I _B = 1 A			1.5	V
Transition frequency	f _T	V _{CE} = 10V, I _C = 1A, f = 0.5MHz		2		MHz
Storage time (L load)	t _{str}	I _C = 4A, I _{B1} = 1A			9	μs
Fall time (L load)	t _f	I _{B2} = -1A, L _{leak} = 5μA			0.8	μs
Storage time (R load)	t _{str}	I _C = 4 A, I _{B1} = 0.8 A		1.5		μs
Fall time (R load)	t _f	I _{B2} = -1.6 A, V _{CC} = 200 V		0.2		μs
Diode forward voltage	V _F	I _C = -5 A, I _B = 0			-2.3	V

Package Dimensions



Inner Circuit





6932852 0016812 247